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**Message**

United States Patent Application No.: 09/890,120

Filed: July 27, 2001

Title: Dynamic Threshold Voltage MOS Transistor Fitted with a Current Limiter, and Processor for Making Such a Transistor

Inventors: Pelloie, et al.

Reference No.: 034299-336

Please find the attached Preliminary Amendment for the above referenced application.

Docket No. 034299-336

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Jean-Luc Pelloie  
SERIAL NO.: 09/890,120  
FILING DATE: July 27, 2001  
TITLE: DYNAMIC THRESHOLD VOLTAGE MOS TRANSISTOR  
FITTED WITH A CURRENT LIMITER, AND PROCESS FOR  
MAKING SUCH A TRANSISTOR  
EXAMINER: Edgardo, Ortiz  
ART UNIT: 2815

#12/E  
PRE-Amend  
J. Meimle  
12/21/02

PRELIMINARY AMENDMENT

Prior to examination, please amend the subject patent application as follows:

IN THE CLAIMS:

Please amend the claims as follows, the amendments which are shown in the  
attached VERSION WITH MARKINGS TO SHOW CHANGES MADE.

1. (Once Amended) A semiconductor device formed on a substrate,  
comprising:  
a first dynamic threshold voltage MOS transistor having a gate and a channel of a  
first conductivity type;

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